

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
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TYPE : 6PT2203N1T**

CHIP SIZE	0.4 * 0.4 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	95,200 pcs

Maximum Ratings(Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	30	V
Gate-source voltage	VGSS	±8	V
Drain Current (DC)	ID	0.7	A

* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			±3	uA	VGS=±8V VDS=0V
2	IDSS			1	uA	VDS=30V VGS=0V
3	BVDSS	32			V	ID=10uA
4	VTH	0.5		1.0	V	ID=250uA VDS=VGS
5	RDS(on)1		0.28	0.4	Ω	ID=200mA VGS=4.5V
6	RDS(on)2		0.39	0.63	Ω	ID=100mA VGS=2.5V
7	RDS(on)3		0.55	1.1	Ω	ID=75mA VGS=1.8V
8	VSD	0.5		1.1	V	I=100mA VGS=0V
9	YFS	200			mS	Vds=10V Id=100mA

※ Built-in ZD between Gate and Source.

NOTE: